Silicon Carbide (SiC) MOSFET – EliteSiC, 20 mohm, 1200 V, M1, TO-247-3L

NTHL020N120SC1

$V_{(BR)DSS}$	$R_{DS(on)}$ MAX	I_D MAX
1200 V	28 mΩ @ 20 V	103 A

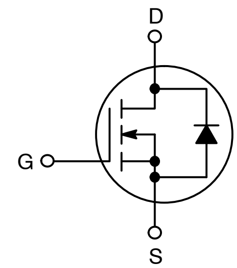
Features

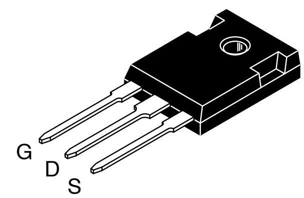
- Typ. $R_{DS(on)}$ = 20 mΩ
- Ultra Low Gate Charge ($Q_{G(tot)}$ = 203 nC)
- Capacitance (C_{oss} = 260 pF)
- 100% UIL Tested
- This Device is Halide Free and RoHS Compliant with exemption 7a, Pb−Free 2LI (on second level interconnection)

Typical Applications

- UPS
- DC−DC Converter
- Boost Inverter

N−CHANNEL MOSFET





TO−247−3LD
CASE 340CX

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Parameter			Symbol	Value	Unit
Drain−to−Source Voltage			V_{DSS}	1200	V
Gate−to−Source Voltage			V_{GS}	−15/+25	V
Recommended Operation Values of Gate−to−Source Voltage	T_C < 175°C		V_{GSop}	−5/+20	V
Continuous Drain Current $R_{\theta JC}$	Steady State	T_C = 25°C	I_D	103	A
Power Dissipation $R_{\theta JC}$			P_D	535	W
Continuous Drain Current $R_{\theta JC}$	Steady State	T_C = 100°C	I_D	73	A
Power Dissipation $R_{\theta JC}$			P_D	267	W
Pulsed Drain Current (Note 2)	T_A = 25°C		I_{DM}	412	A
Operating Junction and Storage Temperature Range			T_J, T_{stg}	−55 to +175	°C
Source Current (Body Diode)			I_S	54	A
Single Pulse Drain−to−Source Avalanche Energy ($I_{L(pk)}$ = 23 A, L = 1 mH) (Note 3)			E_{AS}	264	mJ

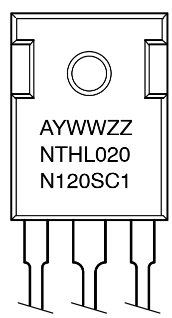
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction−to−Case (Note 1)	$R_{\theta JC}$	0.28	°C/W
Junction−to−Ambient (Note 1)	$R_{\theta JA}$	40	°C/W

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Repetitive rating, limited by max junction temperature.
3. E_{AS} of 264 mJ is based on starting T_J = 25°C; L = 1 mH, I_{AS} = 23 A, V_{DD} = 120 V, V_{GS} = 18 V.

MARKING DIAGRAM



A = Assembly Location
Y = Year
WW = Work Week
ZZ = Lot Traceability
NTHL020N120SC1 = Specific Device Code

ORDERING INFORMATION

Device	Package	Shipping
NTHL160N120SC1	TO−247−3LD	30 Units / Tube

ELECTRICAL CHARACTERISTICS

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain−to−Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 1 mA	1200	–	–	V
Drain−to−Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	I_D = 1 mA, referenced to 25°C	–	900	–	mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS} = 0 V, V_{DS} = 1200 V, T_J = 25°C	–	–	100	μA
		V_{GS} = 0 V, V_{DS} = 1200 V, T_J = 175°C	–	–	250	
Gate−to−Source Leakage Current	I_{GSS}	V_{GS} = +25/−15 V, V_{DS} = 0 V	–	–	±1	μA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(th)}$	V_{GS} = V_{DS}, I_D = 20 mA	1.8	2.7	4.3	V
Recommended Gate Voltage	V_{GOP}		−5	–	+20	V
Drain−to−Source On Resistance	$R_{DS(on)}$	V_{GS} = 20 V, I_D = 60 A, T_J = 25°C	–	20	28	mΩ
		V_{GS} = 20 V, I_D = 60 A, T_J = 175°C	–	35	50	
Forward Transconductance	g_{FS}	V_{DS} = 10 V, I_D = 60 A	–	28	–	S
CHARGES, CAPACITANCES & GATE RESISTANCE						
Input Capacitance	C_{ISS}	V_{GS} = 0 V, f = 1 MHz, V_{DS} = 800 V	–	2890	–	pF
Output Capacitance	C_{OSS}		–	260	–	
Reverse Transfer Capacitance	C_{RSS}		–	22	–	
Total Gate Charge	$Q_{G(tot)}$	V_{GS} = −5/20 V, V_{DS} = 600 V, I_D = 80 A	–	203	–	nC
Threshold Gate Charge	$Q_{G(th)}$		–	33	–	
Gate−to−Source Charge	Q_{GS}		–	66	–	
Gate−to−Drain Charge	Q_{GD}		–	47	–	
Gate Resistance	R_G	f = 1 MHz	–	1.81	–	Ω
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	$t_{d(on)}$	V_{GS} = −5/20 V, V_{DS} = 800 V, I_D = 80 A, R_G = 2 Ω, Inductive Load	–	25	–	ns
Rise Time	t_r		–	57	–	
Turn−Off Delay Time	$t_{d(off)}$		–	45	–	
Fall Time	t_f		–	11	–	
Turn-On Switching Loss	E_{ON}		–	2718	–	μJ
Turn-Off Switching Loss	E_{OFF}		–	326	–	
Total Switching Loss	E_{TOT}		–	3040	–	
DRAIN−SOURCE DIODE CHARACTERISTICS						
Continuous Drain−to−Source Diode Forward Current	I_{SD}	V_{GS} = −5 V, T_J = 25°C	–	–	54	A
Pulsed Drain−to−Source Diode Forward Current (Note 2)	I_{SDM}	V_{GS} = −5 V, T_J = 25°C	–	–	412	A
Forward Diode Voltage	V_{SD}	V_{GS} = −5 V, I_{SD} = 30 A, T_J = 25°C	–	3.7	–	V
Reverse Recovery Time	t_{RR}	V_{GS} = −5/20 V, I_{SD} = 80 A, dI_S/dt = 1000 A/μs	–	31	–	ns
Reverse Recovery Charge	Q_{RR}		–	240	–	nC
Reverse Recovery Energy	E_{REC}		–	10	–	μJ
Peak Reverse Recovery Current	I_{RRM}		–	15	–	A

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS

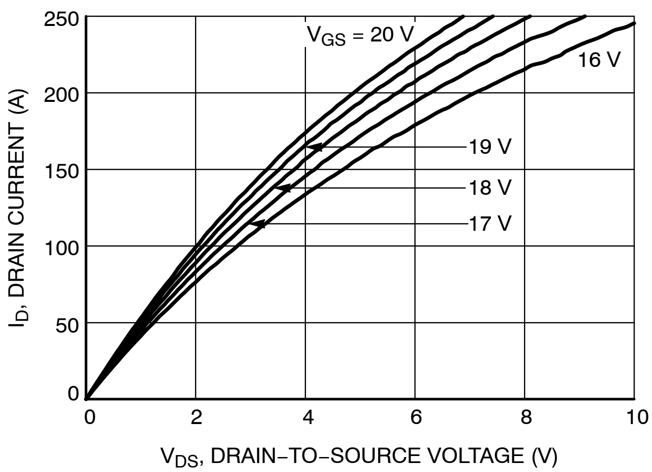


Figure 1. On−Region Characteristics

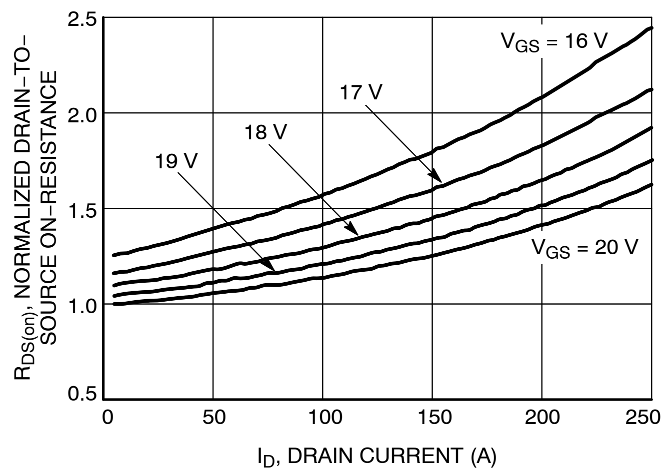


Figure 2. Normalized On−Resistance vs. Drain Current and Gate Voltage

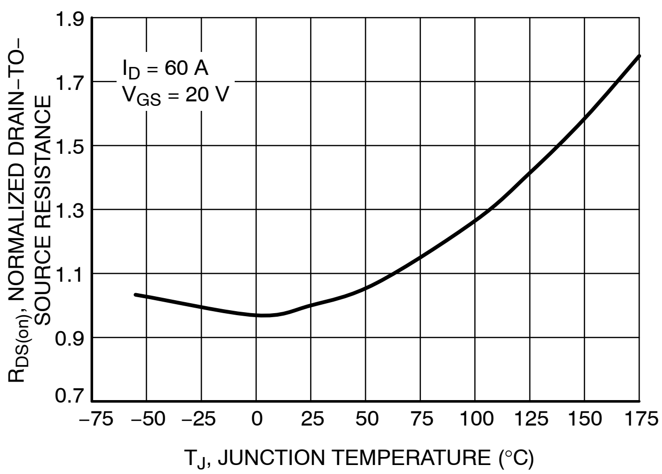


Figure 3. On−Resistance Variation with Temperature

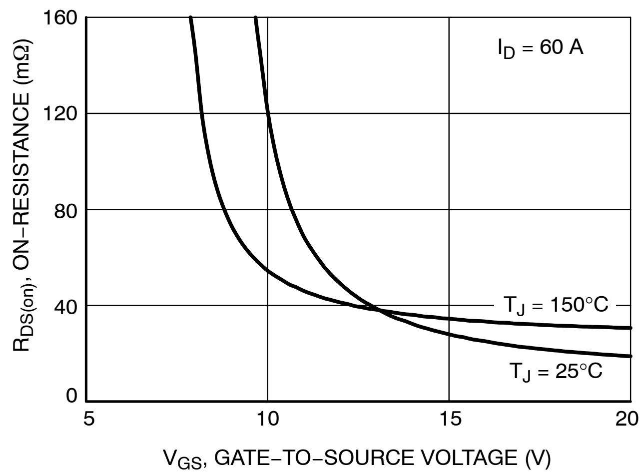


Figure 4. On−Resistance vs. Gate−to−Source Voltage

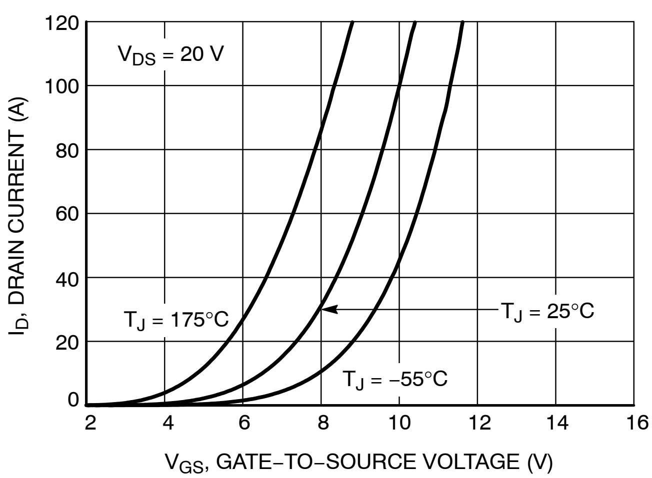


Figure 5. Transfer Characteristics

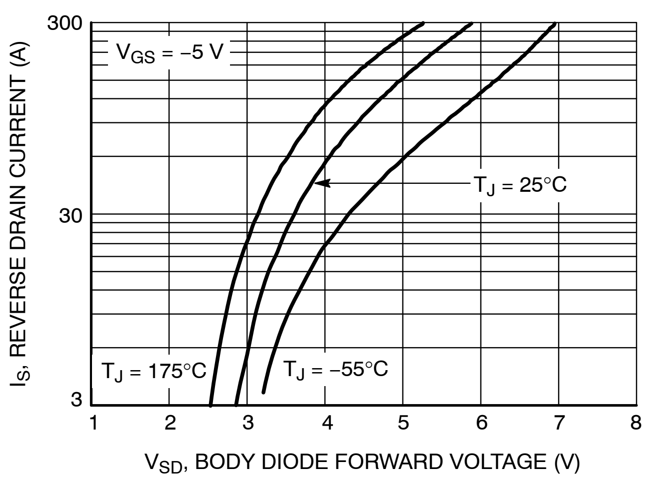


Figure 6. Diode Forward Voltage vs. Current

TYPICAL CHARACTERISTICS (CONTINUED)

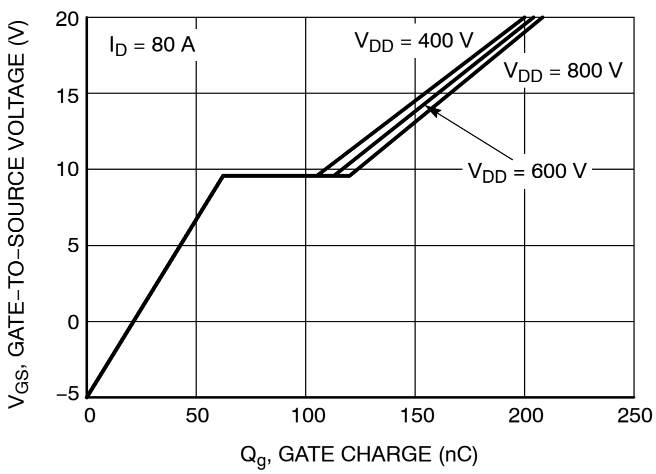


Figure 7. Gate−to−Source Voltage vs. Total Charge

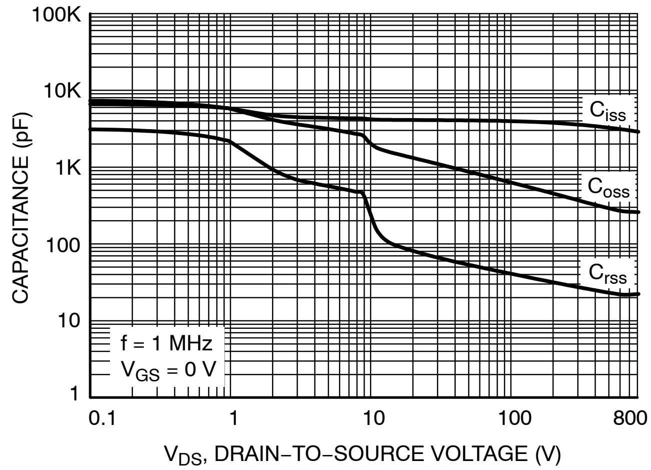


Figure 8. Capacitance vs. Drain−to−Source Voltage

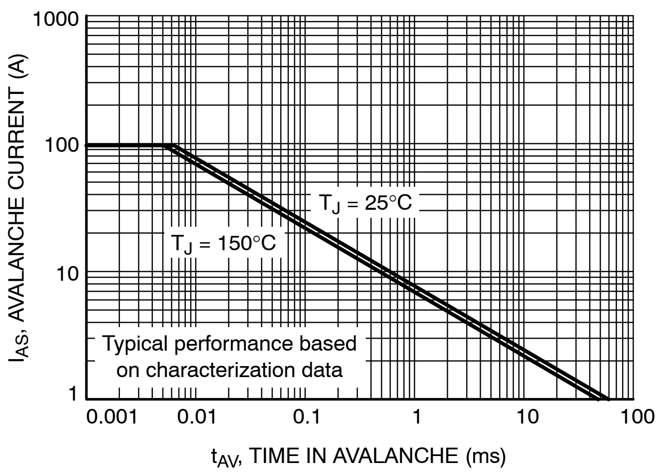


Figure 9. Unclamped Inductive Switching Capability

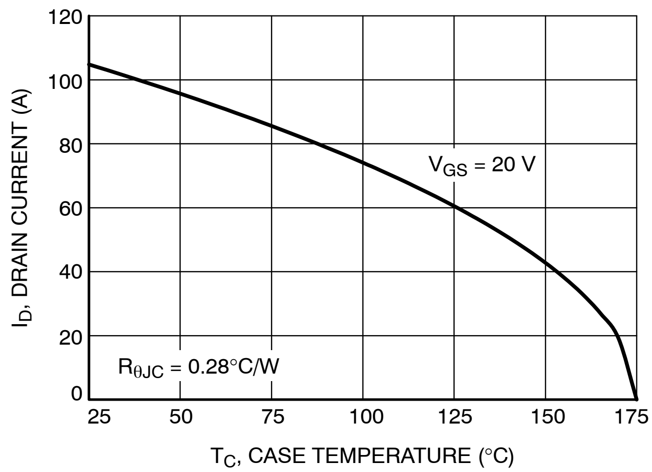


Figure 10. Maximum Continuous Drain Current vs. Case Temperature

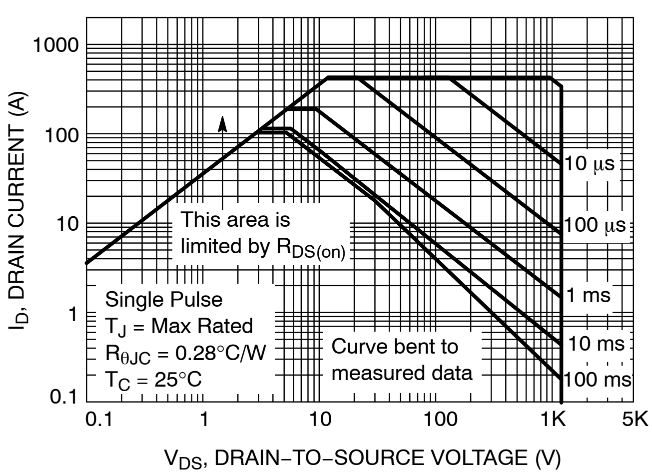


Figure 11. Safe Operating Area

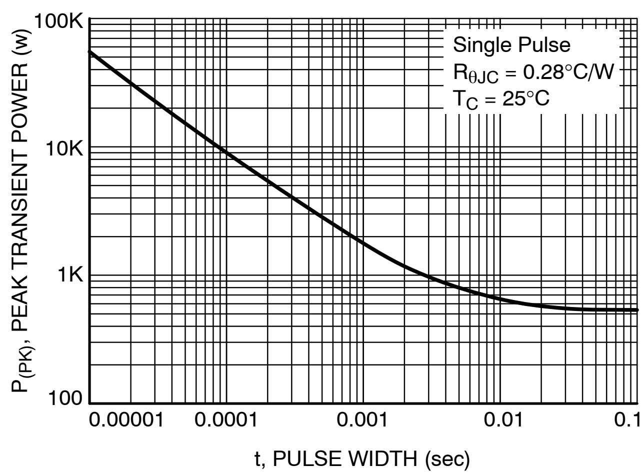


Figure 12. Single Pulse Maximum Power Dissipation

TYPICAL CHARACTERISTICS (CONTINUED)

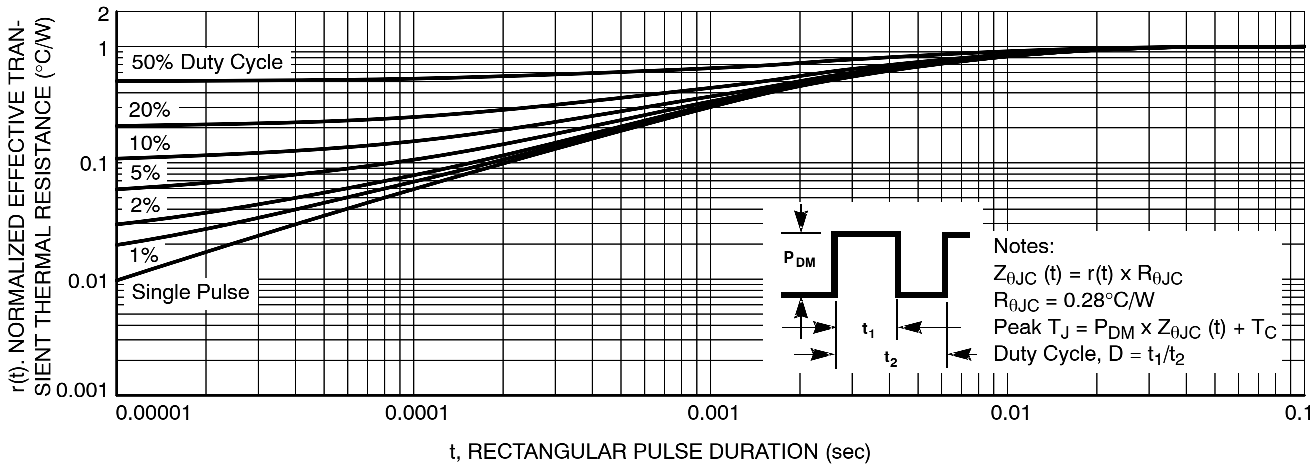
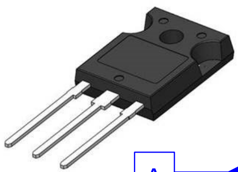
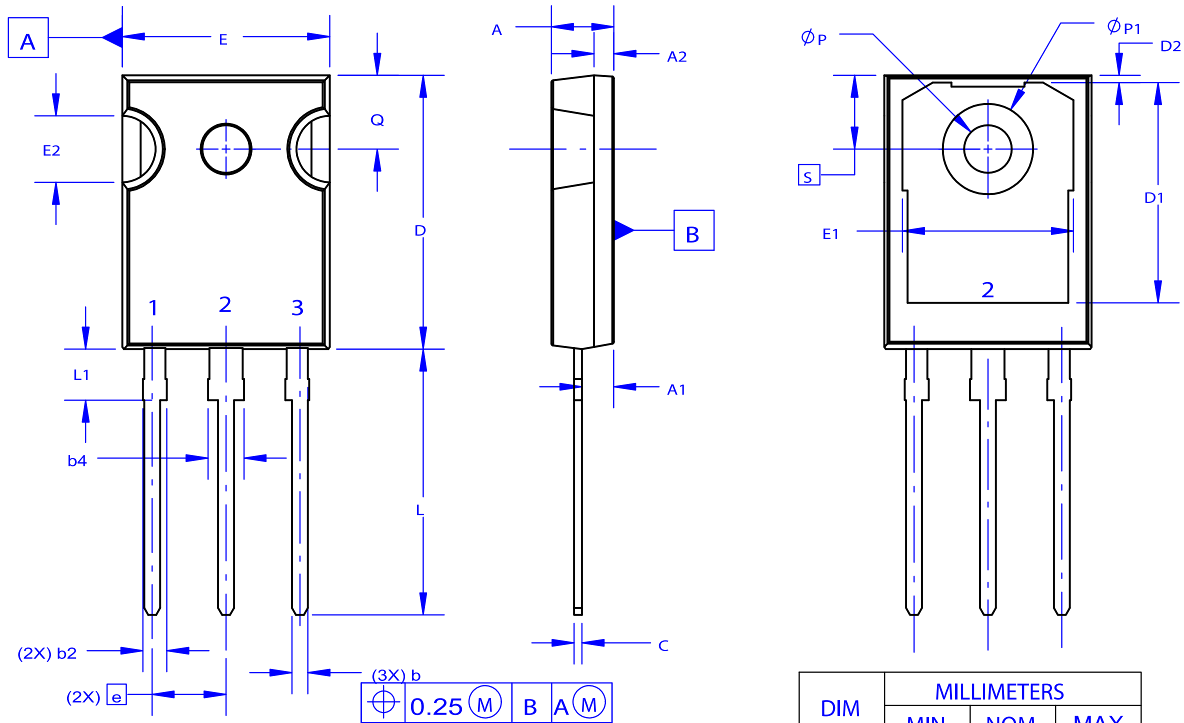


Figure 13. Junction−to−Ambient Thermal Response



TO−247−3LD
CASE 340CX
ISSUE A

DATE 06 JUL 2020

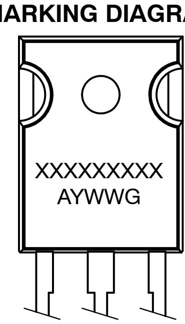


NOTES: UNLESS OTHERWISE SPECIFIED.

A. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
B. ALL DIMENSIONS ARE IN MILLIMETERS.
C. DRAWING CONFORMS TO ASME Y14.5 - 2009.
D. DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED BY L1.
E. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	4.58	4.70	4.82
A1	2.20	2.40	2.60
A2	1.40	1.50	1.60
D	20.32	20.57	20.82
E	15.37	15.62	15.87
E2	4.96	5.08	5.20
e	~	5.56	~
L	19.75	20.00	20.25
L1	3.69	3.81	3.93
ØP	3.51	3.58	3.65
Q	5.34	5.46	5.58
S	5.34	5.46	5.58
b	1.17	1.26	1.35
b2	1.53	1.65	1.77
b4	2.42	2.54	2.66
c	0.51	0.61	0.71
D1	13.08	~	~
D2	0.51	0.93	1.35
E1	12.81	~	~
ØP1	6.60	6.80	7.00

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
G = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “ ▪”, may or may not be present. Some products may not follow the Generic Marking.

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